

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
650V	190mΩ@10V	21A

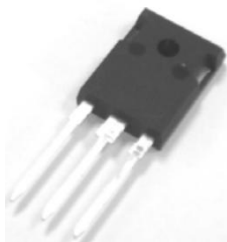
Feature

- Low on-resistance
- Low gate charge

Application

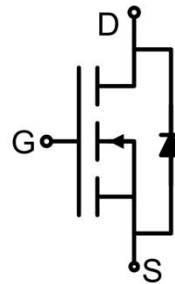
- Power factor correction (PFC)
- Uninterruptible Power Supply (UPS)

Package



TO-247AB

Circuit diagram



Marking



Absolute maximum ratings (T_c=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage (V _{GS} =0V)	V _{DS}	650	V
Gate-Source Voltage	V _{GS}	±30	V
Continuous Drain Current	I _D	21	A
Pulsed Drain Current ¹⁾	I _{DM}	50	A
Single Pulse Avalanche Energy ²⁾	E _{AS}	500	mJ
Power Dissipation ³⁾	P _D	150	W
Thermal Resistance Junction to Case	R _{θJC}	0.82	°C/W
Operating Junction Temperature	T _J	-55 ~ +150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

Electrical characteristics (T_J=25 °C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250μA	650			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =650V, V _{GS} =0V			1	μA
Gate-body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±30V			±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.5	3.3	4.5	V
Drain-source on-resistance	R _{DS(on)}	V _{GS} =10V, I _D =3.2A		150	190	mΩ
Dynamic characteristics ⁴⁾						
Input Capacitance	C _{iss}	V _{DS} =100V, V _{GS} =0V, f =1MHz		1510		pF
Output Capacitance	C _{oss}			65		
Reverse Transfer Capacitance	C _{rss}			2.4		
Total Gate Charge	Q _g	V _{DS} =480V, V _{GS} =10V, I _D =11A		7.27		nC
Gate-Source Charge	Q _{gs}			17.4		
Gate-Drain Charge	Q _{gd}			43.9		
Turn-on delay time	t _{d(on)}	V _{DS} =400V, V _{GS} =13V, I _D =13A R _G =4.7Ω		10		nS
Turn-on rise time	t _r			19.8		
Turn-off delay time	t _{d(off)}			45.4		
Turn-off fall time	t _f			41.4		
Source-Drain Diode characteristics						
Diode Forward Current	I _S				21	A
Diode Forward voltage	V _{SD}	V _{GS} =0V, I _S =7.3A			1.5	V
Reverse Recovery Time	T _{rr}	V _{GS} =0V, V _{dd} =400V, I _S =11A di/dt =100A/μs		288		nS
Reverse Recovery Charge	Q _{rr}			3.66		uC

Notes:

- 1) The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2) The EAS data shows Max. rating . L=0.5mH, I_{AS} =7A, V_{DD} =50V, R_G =25Ω.
- 3) The power dissipation is limited by 150°C junction temperature.
- 4) Guaranteed by design, not subject to production testing.

Typical Characteristics

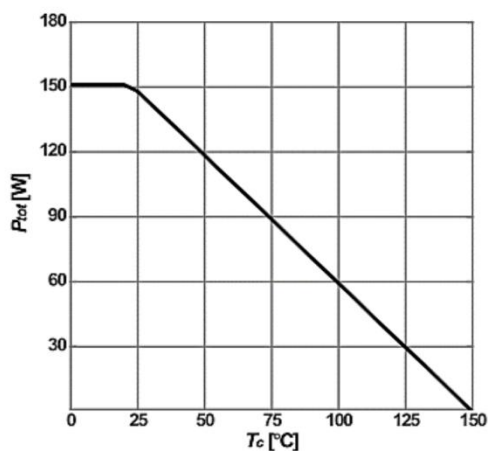


Figure1: Power dissipation (Non FullPAK)

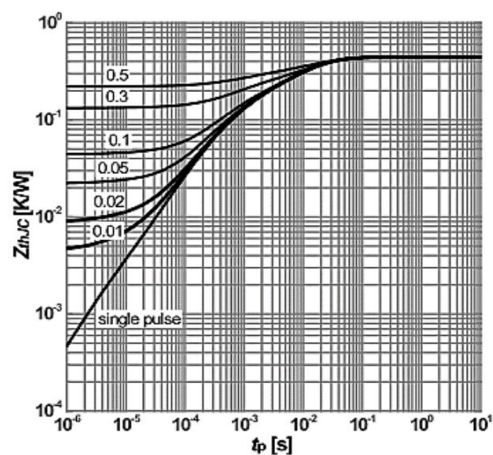


Figure2:Max. transient thermal impedance

$Z_{thJC}=f(t_p)$; parameter: $D = t_p/T$

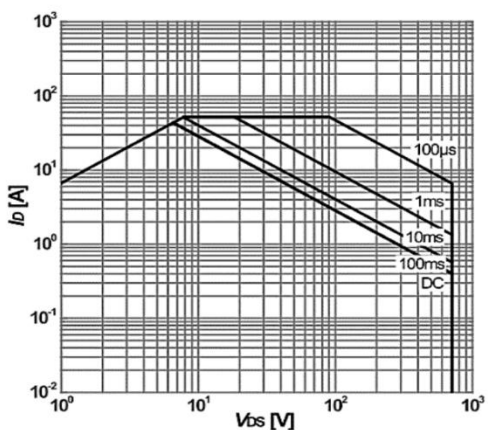


Figure 3 : Safe operating area (Non FullPAK)

$I_D=f(V_{DS})$; $T_J=25^{\circ}\text{C}$; $D=0$; parameter: t_p

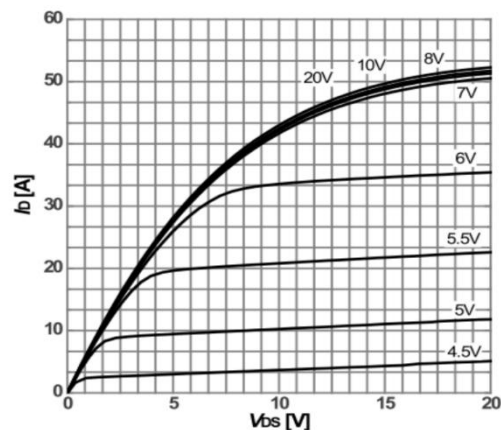


Figure 4 : Typ. output characteristics

$R_{DS(on)}=f(T_J)$; $I_D=3.2\text{A}$; $V_{GS}=10\text{V}$

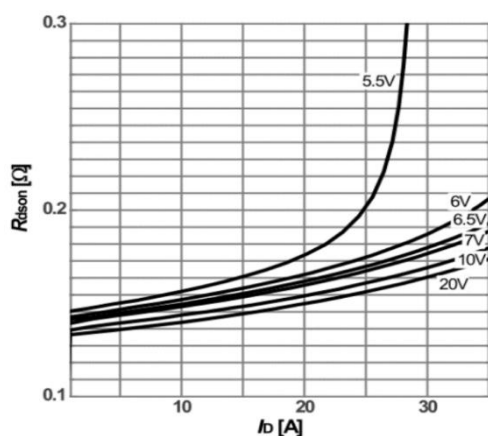
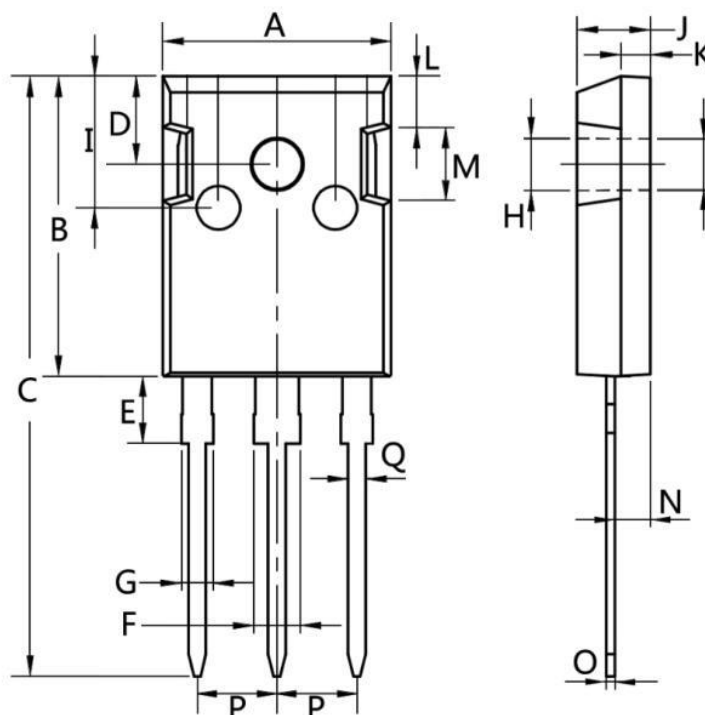


Figure 5 : Type. gate charge

$R_{DS(on)}=f(I_D)$; $T_J=25^{\circ}\text{C}$; parameter: V_{GS}

TO-247AB Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	15.000	16.000	0.591	0.630
B	20.000	21.000	0.787	0.827
C	41.000	42.000	1.614	1.654
D	5.000	6.000	0.197	0.236
E	4.000	5.000	0.157	0.197
F	2.500	3.500	0.098	0.138
G	1.750	2.500	0.069	0.098
H	3.000	3.500	0.118	0.138
I	8.000	10.000	0.315	0.394
J	4.900	5.100	0.193	0.201
K	1.900	2.100	0.075	0.083
L	3.500	4.000	0.138	0.157
M	4.750	5.250	0.187	0.207
N	2.000	3.000	0.079	0.118
O	0.550	0.750	0.022	0.030
P	5.080 BSC.		0.200 BSC.	
Q	1.200	1.300	0.047	0.051